

Mode Field Effect Transistor

Product Summary

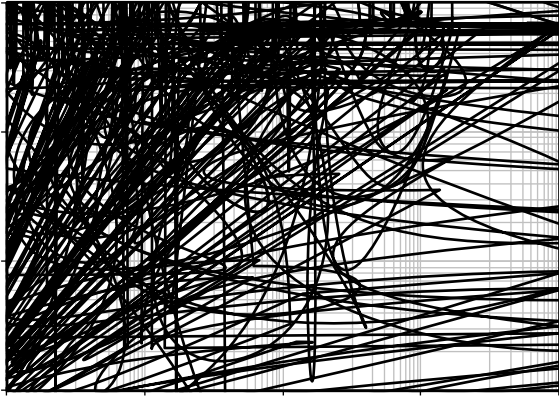
V_{DS}	-60 V
I_D	-100 A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	8.8m
$R_{DS(ON)}$ (at $V_{GS}=-6V$)	10m
100% EAS Tested.1	



Electrical Characteristics ($T_J=25$ unless otherwise noted)

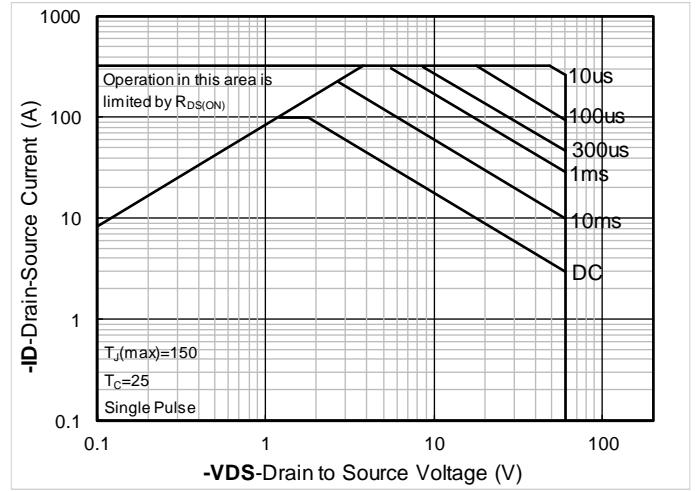
Parameter	Symbol	Conditions	Min	Typ	Max
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YJB100GP06H



0001 Vt 10u 1a m

Figure 13. Maximum Transient Thermal Impedance



Figure



TO-263-HY Package information

SYM.	MIN.
A2	
b2	0.050
c	
c2	
D2	
E	
E1	



Disclaimer

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